

2SC5820

Silicon NPN Epitaxial High Frequency Low Noise Amplifier / Oscillator

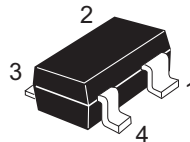
REJ03G0758-0200
(Previous ADE-208-1604A)
Rev.2.00
Aug.10.2005

Application

- High gain bandwidth product
 $f_T = 20 \text{ GHz typ.}$
- High power gain and low noise figure;
 $PG = 17.5 \text{ dB typ.}, NF = 1.15 \text{ dB typ. at } f = 1.8 \text{ GHz}$

Outline

RENESAS Package code: PTSP0004ZA-A
(Package name: CMPAK-4)



1. Emitter
2. Collector
3. Emitter
4. Base

Note: Marking is "WU-".

Absolute Maximum Ratings

($T_a = 25^\circ\text{C}$)

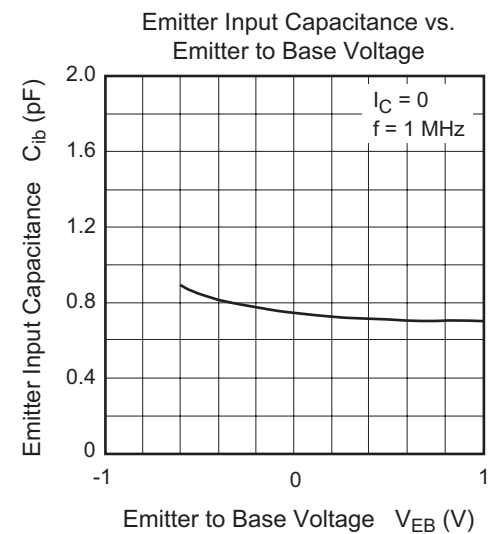
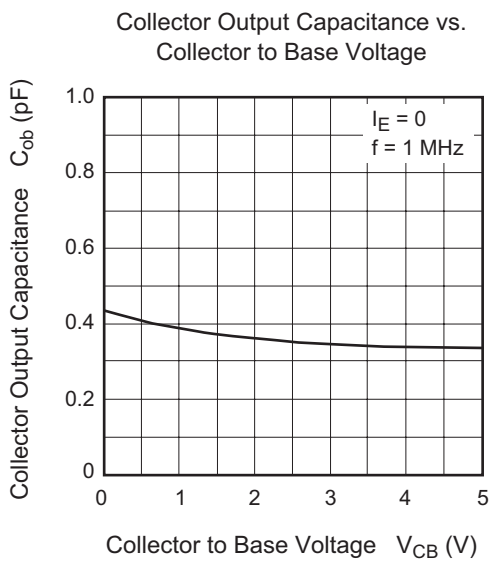
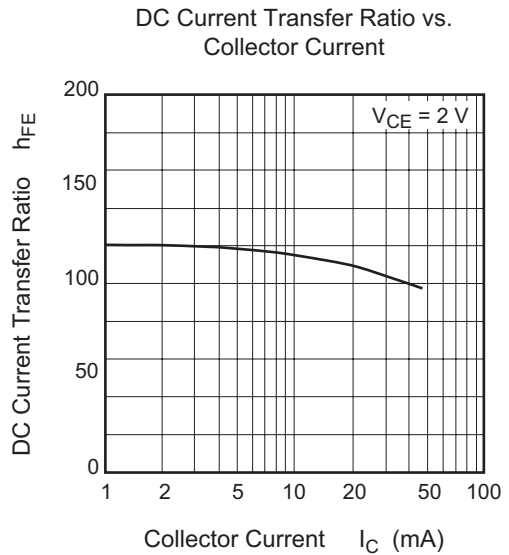
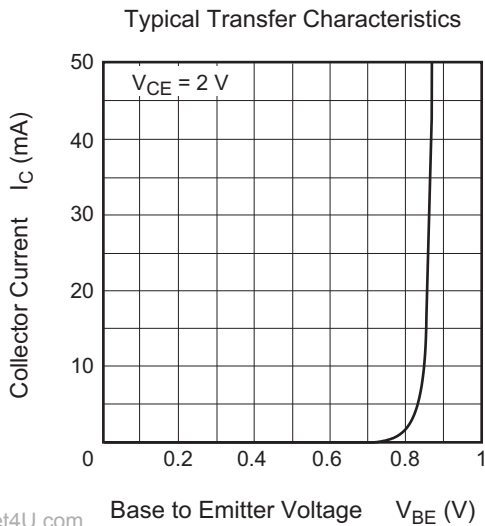
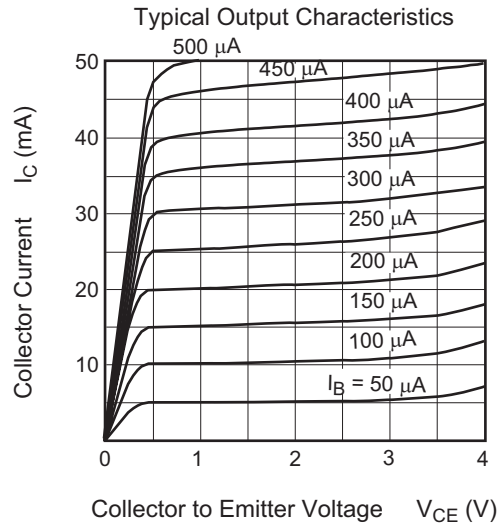
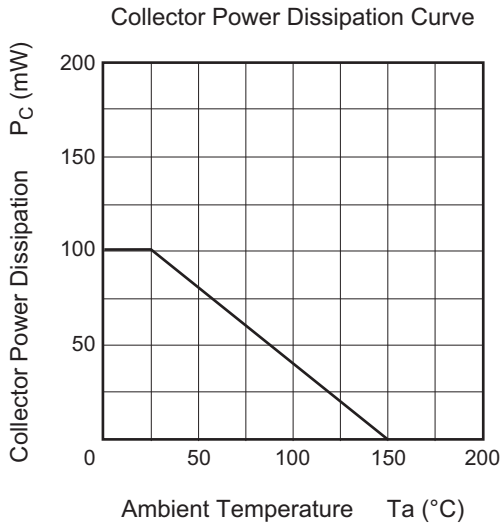
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	12	V
Collector to emitter voltage	V_{CEO}	4.0	V
Emitter to base voltage	V_{EBO}	1.5	V
Collector current	I_C	35	mA
Collector power dissipation	P_C	100	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

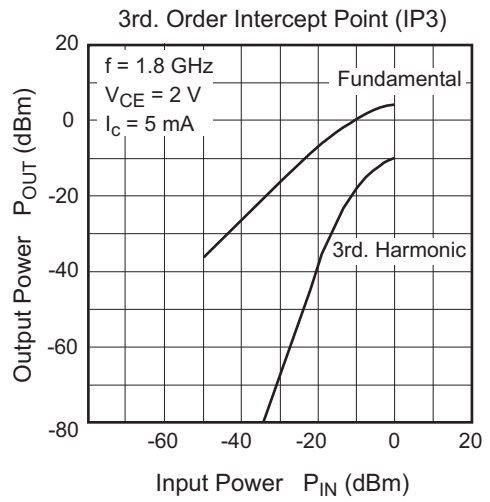
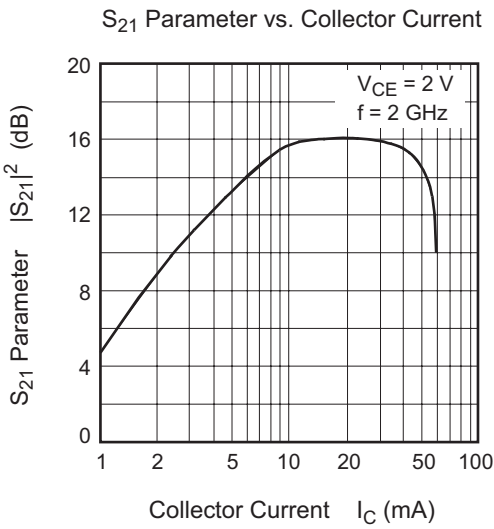
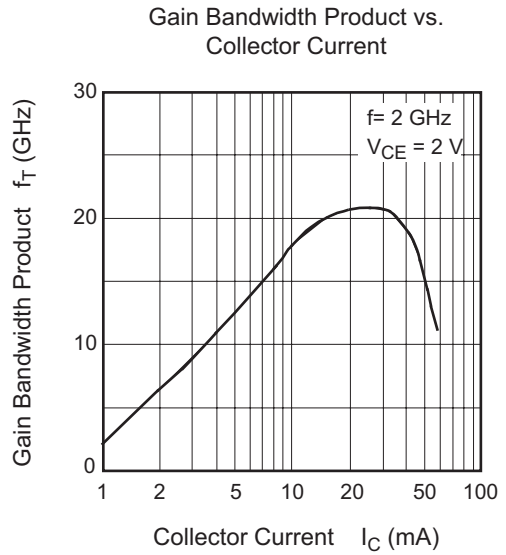
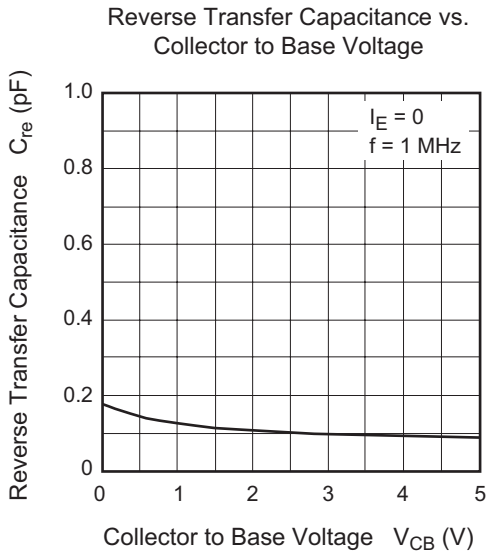
Electrical Characteristics

(Ta = 25°C)

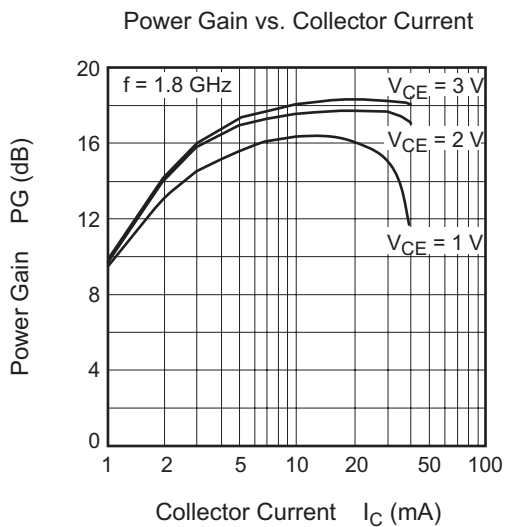
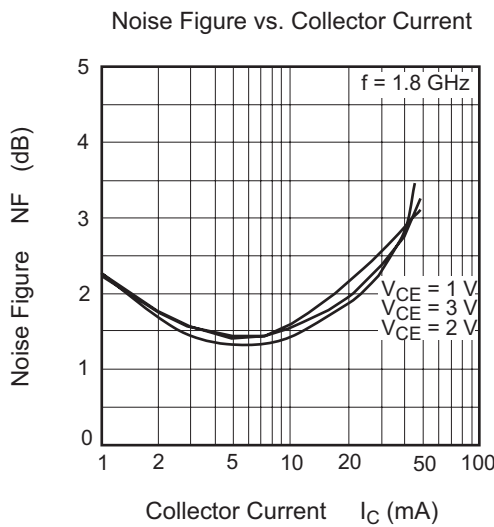
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector cutoff current	I_{CBO}	—	—	1	μA	$V_{CB} = 12 V, I_E = 0$
Collector cutoff current	I_{CEO}	—	—	1	μA	$V_{CE} = 4 V, R_{BE} = \infty$
Emitter cutoff current	I_{EBO}	—	—	10	μA	$V_{EB} = 1.5 V, I_C = 0$
DC current transfer ratio	h_{FE}	70	110	150	—	$V_{CE} = 2 V, I_C = 20 mA$
Collector output capacitance	C_{ob}	—	0.3	0.6	pF	$V_{CB} = 2 V, I_E = 0, f = 1 MHz$
Gain bandwidth product	f_T	17	20	—	GHz	$V_{CE} = 2 V, I_C = 30 mA$ $f = 2 GHz$
Power gain	PG	13	17.5	—	dB	$V_{CE} = 2 V, I_C = 30 mA,$ $f = 1.8 GHz$
Noise figure	NF	—	1.15	1.7	dB	$V_{CE} = 2 V, I_C = 5 mA,$ $f = 1.8 GHz$
3rd. Order Intercept Point	IP3	—	10	—	dBm	$V_{CE} = 2 V, I_C = 5 mA,$ $f = 1.8 GHz$

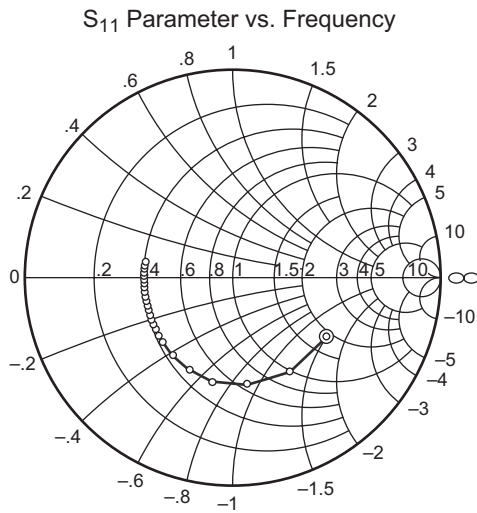
Main Characteristics



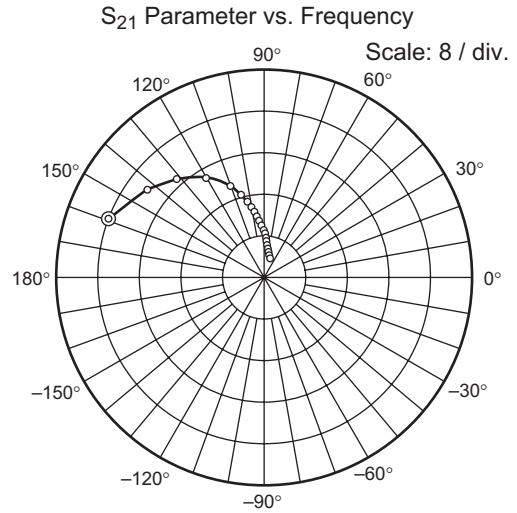


www.DataSheet4U.com

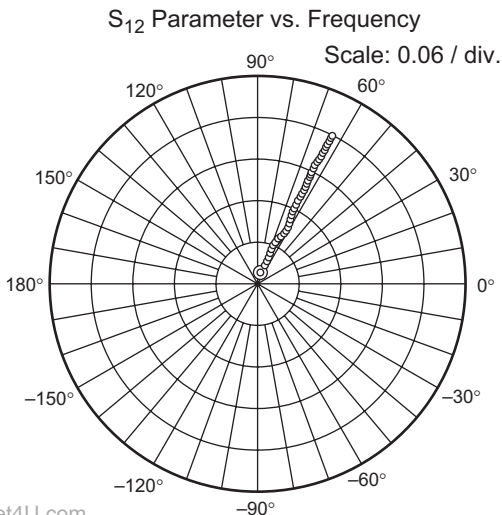




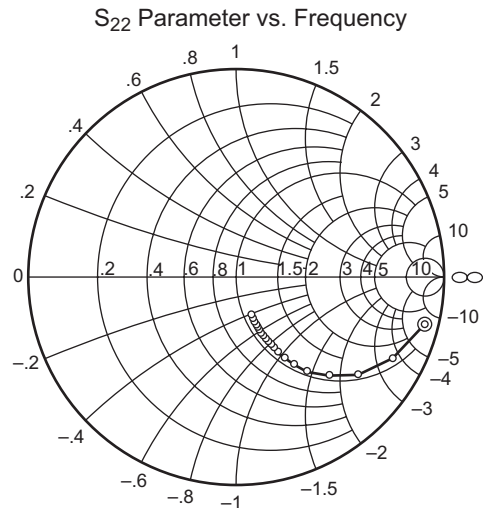
Condition: $V_{CE} = 2\text{ V}$, $Z_O = 50\ \Omega$
 100 to 3000 MHz (100 MHz Step)
 ⊙—○ ($I_C = 30\text{ mA}$)



Condition: $V_{CE} = 2\text{ V}$, $Z_O = 50\ \Omega$
 100 to 3000 MHz (100 MHz Step)
 ⊙—○ ($I_C = 30\text{ mA}$)



Condition: $V_{CE} = 2\text{ V}$, $Z_O = 50\ \Omega$
 100 to 3000 MHz (100 MHz Step)
 ⊙—○ ($I_C = 30\text{ mA}$)



Condition: $V_{CE} = 2\text{ V}$, $Z_O = 50\ \Omega$
 100 to 3000 MHz (100 MHz Step)
 ⊙—○ ($I_C = 30\text{ mA}$)

www.DataSheet4U.com

S Parameter

 $(V_{CE} = 2\text{ V}, I_C = 5\text{ mA}, Z_O = 50\ \Omega)$

f (MHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100	0.844	-24.6	15.26	159.9	0.0124	78.9	0.976	-16.4
200	0.835	-23.1	15.07	162.9	0.0153	84.0	0.973	-11.7
300	0.838	-34.2	14.59	154.8	0.0236	80.2	0.953	-17.5
400	0.809	-45.7	13.94	147.1	0.0311	72.5	0.919	-23.6
500	0.781	-56.2	13.16	139.9	0.0387	67.5	0.879	-29.0
600	0.745	-66.8	12.39	133.1	0.0441	61.6	0.828	-33.9
700	0.710	-76.0	11.71	127.7	0.0506	56.2	0.779	-38.6
800	0.688	-85.5	10.89	121.8	0.0537	52.0	0.728	-41.9
900	0.659	-93.5	10.16	117.0	0.0579	47.7	0.682	-45.4
1000	0.639	-101.0	9.47	112.8	0.0610	46.8	0.641	-47.4
1100	0.633	-107.3	8.77	108.6	0.0643	41.1	0.601	-49.8
1200	0.596	-115.4	8.40	105.2	0.0640	40.4	0.560	-51.8
1300	0.578	-121.8	7.92	101.5	0.0665	37.6	0.528	-54.0
1400	0.570	-128.0	7.47	98.3	0.0675	37.4	0.499	-55.4
1500	0.556	-133.1	7.04	95.6	0.0685	32.9	0.473	-57.1
1600	0.548	-138.8	6.68	92.5	0.0691	32.9	0.449	-58.0
1700	0.541	-143.6	6.37	90.1	0.0693	32.5	0.422	-59.0
1800	0.532	-149.0	6.08	87.5	0.0699	30.2	0.400	-60.6
1900	0.529	-153.1	5.77	85.0	0.0716	30.6	0.384	-60.7
2000	0.523	-157.1	5.53	83.2	0.0735	28.8	0.370	-62.1
2100	0.520	-162.0	5.29	80.4	0.0719	30.4	0.349	-62.5
2200	0.521	-164.7	5.03	79.1	0.0733	28.1	0.345	-63.6
2300	0.521	-168.8	4.86	76.4	0.0752	26.6	0.326	-64.0
2400	0.521	-172.0	4.67	74.4	0.0748	26.8	0.312	-64.8
2500	0.520	-175.7	4.53	72.3	0.0752	26.8	0.297	-65.6
2600	0.522	-178.4	4.33	70.6	0.0765	26.2	0.292	-66.7
2700	0.525	-178.2	4.21	68.6	0.0771	27.6	0.280	-67.8
2800	0.526	-175.6	4.05	67.2	0.0775	27.4	0.275	-68.9
2900	0.529	-172.4	3.91	64.8	0.0785	25.5	0.260	-69.5
3000	0.532	-169.7	3.82	62.7	0.0772	24.6	0.249	-70.5

(V_{CE} = 2 V, I_C = 10 mA, Z_O = 50 Ω)

f (MHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100	0.717	-17.3	25.92	167.8	0.0073	84.9	0.967	-8.4
200	0.712	-34.2	24.87	156.2	0.0137	81.4	0.941	-17.1
300	0.699	-50.1	23.25	145.5	0.0205	73.7	0.896	-25.1
400	0.667	-65.5	21.32	136.0	0.0266	66.0	0.833	-32.8
500	0.635	-78.9	19.27	127.6	0.0319	62.0	0.766	-39.1
600	0.600	-91.5	17.37	120.5	0.0349	56.4	0.694	-44.3
700	0.572	-102.0	15.73	115.1	0.0403	52.7	0.632	-48.6
800	0.553	-112.1	14.26	109.6	0.0402	51.2	0.574	-51.7
900	0.533	-120.1	12.97	105.3	0.0445	46.0	0.525	-54.8
1000	0.522	-127.4	11.90	101.6	0.0472	47.2	0.484	-56.2
1100	0.515	-133.7	10.90	98.1	0.0476	43.4	0.446	-58.4
1200	0.499	-140.9	10.16	95.3	0.0477	44.4	0.410	-59.4
1300	0.492	-146.8	9.46	92.2	0.0505	43.3	0.381	-61.0
1400	0.490	-152.1	8.84	89.6	0.0509	43.8	0.357	-61.9
1500	0.484	-156.6	8.27	87.4	0.0520	39.7	0.335	-62.9
1600	0.484	-161.3	7.79	84.8	0.0533	41.0	0.316	-63.4
1700	0.482	-165.3	7.38	82.8	0.0540	41.4	0.295	-64.0
1800	0.481	-169.8	6.99	80.7	0.0548	40.0	0.277	-65.0
1900	0.481	-173.1	6.63	78.7	0.0578	41.6	0.265	-65.1
2000	0.481	-176.4	6.33	76.9	0.0601	39.9	0.252	-66.1
2100	0.483	179.9	6.02	74.8	0.0603	42.3	0.238	-66.1
2200	0.484	177.3	5.75	73.4	0.0610	39.9	0.232	-66.9
2300	0.488	174.4	5.52	71.4	0.0641	39.3	0.219	-67.2
2400	0.489	171.8	5.29	69.6	0.0646	39.5	0.209	-67.7
2500	0.491	169.0	5.10	67.8	0.0664	40.2	0.197	-68.0
2600	0.495	166.5	4.89	66.2	0.0678	39.7	0.194	-69.7
2700	0.501	164.3	4.73	64.6	0.0693	40.4	0.185	-71.0
2800	0.503	161.9	4.55	63.2	0.0705	40.2	0.181	-71.9
2900	0.508	159.6	4.39	61.4	0.0715	39.5	0.170	-72.9
3000	0.510	157.3	4.27	59.6	0.0717	37.3	0.162	-74.0

(V_{CE} = 2 V, I_C = 20 mA, Z_O = 50 Ω)

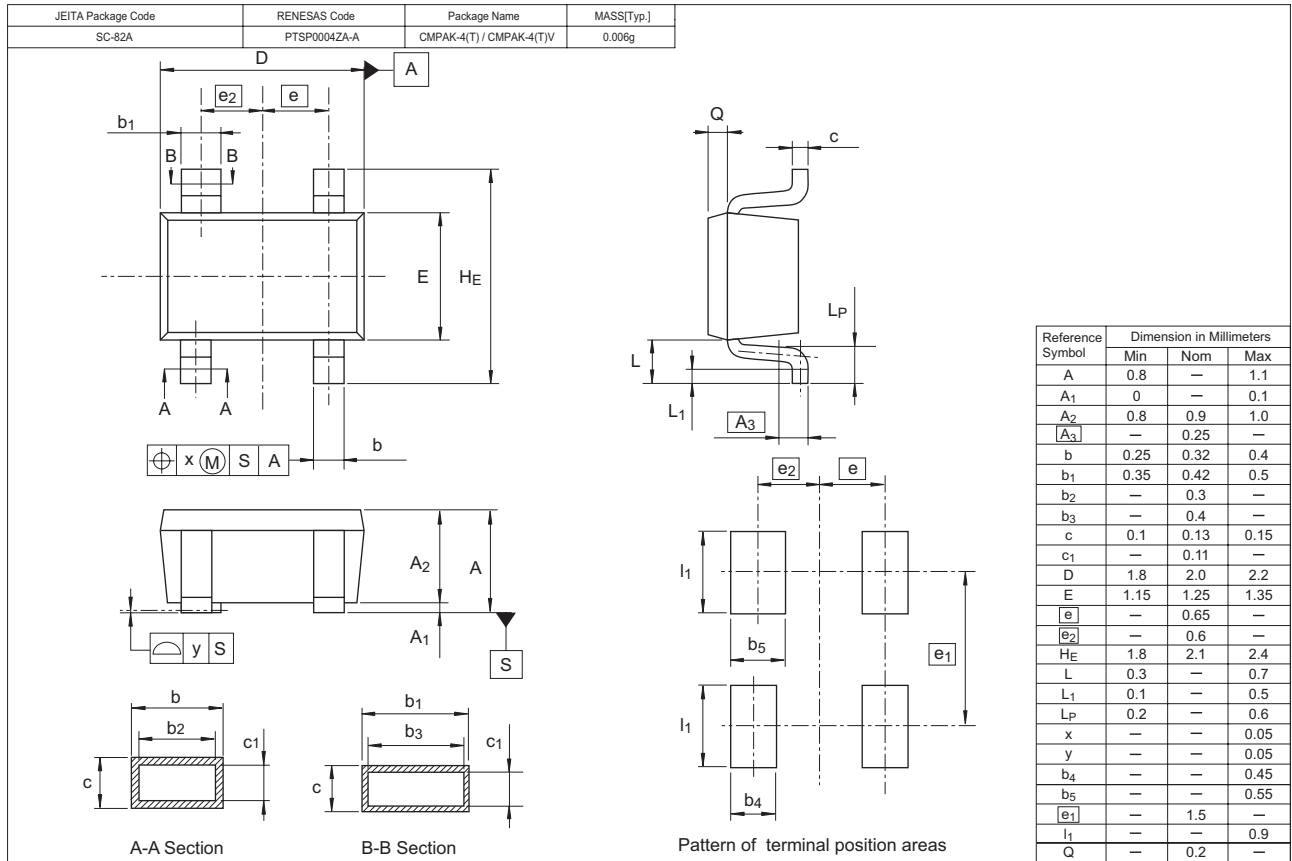
f (MHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100	0.556	-26.3	38.68	163.4	0.0065	88.2	0.937	-11.6
200	0.550	-50.8	35.60	148.3	0.0117	78.3	0.882	-23.2
300	0.537	-72.0	31.52	135.5	0.0174	71.3	0.805	-32.9
400	0.519	-90.7	27.37	125.0	0.0215	63.3	0.716	-41.4
500	0.501	-105.4	23.66	116.7	0.0252	62.0	0.633	-47.6
600	0.485	-118.3	20.55	110.2	0.0276	57.0	0.556	-52.3
700	0.475	-128.1	18.10	105.3	0.0310	54.2	0.495	-55.9
800	0.470	-137.3	16.09	100.7	0.0312	54.1	0.441	-58.4
900	0.462	-144.3	14.43	97.1	0.0352	51.7	0.397	-60.8
1000	0.460	-150.4	13.12	94.1	0.0369	53.1	0.362	-61.7
1100	0.460	-155.8	11.95	91.2	0.0389	50.4	0.330	-63.6
1200	0.458	-161.4	11.00	88.9	0.0397	52.5	0.302	-63.5
1300	0.457	-166.3	10.20	86.4	0.0425	51.5	0.280	-64.7
1400	0.460	-170.1	9.48	84.2	0.0441	53.3	0.260	-65.2
1500	0.457	-173.9	8.85	82.2	0.0452	49.4	0.242	-66.3
1600	0.462	-177.4	8.31	80.0	0.0469	50.7	0.227	-65.9
1700	0.462	179.3	7.84	78.4	0.0478	52.0	0.210	-66.4
1800	0.466	175.9	7.41	76.6	0.0496	49.7	0.198	-66.8
1900	0.467	173.3	7.02	74.8	0.0532	51.5	0.187	-67.2
2000	0.469	170.6	6.70	73.2	0.0548	50.1	0.178	-67.2
2100	0.474	167.8	6.36	71.4	0.0572	52.8	0.167	-67.3
2200	0.476	165.5	6.09	70.0	0.0574	50.9	0.161	-68.3
2300	0.480	163.3	5.82	68.3	0.0610	48.6	0.152	-68.2
2400	0.483	161.2	5.58	66.7	0.0616	49.0	0.143	-69.2
2500	0.486	159.0	5.37	65.0	0.0638	49.8	0.135	-69.8
2600	0.490	156.9	5.15	63.4	0.0661	48.6	0.131	-70.8
2700	0.497	155.3	4.97	62.1	0.0699	48.9	0.123	-72.9
2800	0.499	153.1	4.78	60.8	0.0715	49.3	0.122	-74.1
2900	0.505	151.4	4.61	59.2	0.0714	48.0	0.114	-75.4
3000	0.506	149.6	4.48	57.6	0.0713	46.7	0.106	-77.2

www.DataSheet4U.com

(V_{CE} = 2 V, I_C = 30 mA, Z_O = 50 Ω)

f (MHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100	0.441	-34.8	45.76	160.6	0.0061	84.2	0.913	-13.6
200	0.449	-65.1	40.75	143.5	0.0110	78.8	0.838	-26.7
300	0.455	-88.7	34.81	129.9	0.0153	69.4	0.741	-37.1
400	0.455	-107.9	29.32	119.4	0.0185	63.3	0.641	-45.5
500	0.451	-122.1	24.83	111.5	0.0223	61.5	0.558	-51.2
600	0.450	-133.9	21.25	105.6	0.0238	58.6	0.485	-55.6
700	0.449	-142.5	18.53	101.1	0.0280	55.9	0.428	-58.5
800	0.451	-150.6	16.36	97.0	0.0284	57.8	0.378	-60.4
900	0.449	-156.4	14.62	93.7	0.0321	55.5	0.340	-62.8
1000	0.449	-161.7	13.25	91.1	0.0347	57.7	0.308	-63.1
1100	0.453	-166.3	12.05	88.4	0.0360	55.5	0.279	-64.9
1200	0.455	-171.0	11.05	86.3	0.0364	58.0	0.256	-64.1
1300	0.457	-175.0	10.23	84.0	0.0399	56.7	0.236	-65.2
1400	0.460	-178.3	9.50	82.0	0.0413	58.5	0.220	-65.5
1500	0.460	178.5	8.86	80.2	0.0438	54.8	0.204	-66.2
1600	0.466	175.5	8.32	78.1	0.0437	55.1	0.190	-65.9
1700	0.466	172.7	7.84	76.5	0.0465	56.5	0.176	-65.8
1800	0.471	169.8	7.41	74.8	0.0481	55.4	0.165	-66.4
1900	0.472	167.4	7.02	73.2	0.0517	56.0	0.157	-66.9
2000	0.476	165.0	6.69	71.6	0.0540	54.4	0.149	-66.8
2100	0.480	162.7	6.35	69.9	0.0560	56.9	0.139	-67.3
2200	0.483	160.5	6.08	68.5	0.0573	55.2	0.134	-67.8
2300	0.487	158.7	5.81	66.9	0.0604	52.3	0.126	-67.7
2400	0.489	156.8	5.56	65.4	0.0617	53.6	0.117	-68.2
2500	0.493	154.9	5.35	63.8	0.0633	53.4	0.110	-68.8
2600	0.497	153.0	5.14	62.2	0.0659	51.6	0.107	-70.8
2700	0.504	151.6	4.96	60.9	0.0690	52.2	0.101	-72.8
2800	0.507	149.5	4.77	59.6	0.0711	52.9	0.099	-73.4
2900	0.511	148.0	4.59	58.1	0.0714	50.9	0.091	-76.1
3000	0.515	146.3	4.47	56.5	0.0717	49.4	0.085	-78.0

Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SC5820WU-TL-E	3000	φ 178 mm Reel, 8 mm Emboss Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

Renesas Technology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

Keep safety first in your circuit designs!

1. Renesas Technology Corp. puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

Notes regarding these materials

1. These materials are intended as a reference to assist our customers in the selection of the Renesas Technology Corp. product best suited to the customer's application; they do not convey any license under any intellectual property rights, or any other rights, belonging to Renesas Technology Corp. or a third party.
2. Renesas Technology Corp. assumes no responsibility for any damage, or infringement of any third-party's rights, originating in the use of any product data, diagrams, charts, programs, algorithms, or circuit application examples contained in these materials.
3. All information contained in these materials, including product data, diagrams, charts, programs and algorithms represents information on products at the time of publication of these materials, and are subject to change by Renesas Technology Corp. without notice due to product improvements or other reasons. It is therefore recommended that customers contact Renesas Technology Corp. or an authorized Renesas Technology Corp. product distributor for the latest product information before purchasing a product listed herein.
The information described here may contain technical inaccuracies or typographical errors.
Renesas Technology Corp. assumes no responsibility for any damage, liability, or other loss rising from these inaccuracies or errors.
Please also pay attention to information published by Renesas Technology Corp. by various means, including the Renesas Technology Corp. Semiconductor home page (<http://www.renesas.com>).
4. When using any or all of the information contained in these materials, including product data, diagrams, charts, programs, and algorithms, please be sure to evaluate all information as a total system before making a final decision on the applicability of the information and products. Renesas Technology Corp. assumes no responsibility for any damage, liability or other loss resulting from the information contained herein.
5. Renesas Technology Corp. semiconductors are not designed or manufactured for use in a device or system that is used under circumstances in which human life is potentially at stake. Please contact Renesas Technology Corp. or an authorized Renesas Technology Corp. product distributor when considering the use of a product contained herein for any specific purposes, such as apparatus or systems for transportation, vehicular, medical, aerospace, nuclear, or undersea repeater use.
6. The prior written approval of Renesas Technology Corp. is necessary to reprint or reproduce in whole or in part these materials.
7. If these products or technologies are subject to the Japanese export control restrictions, they must be exported under a license from the Japanese government and cannot be imported into a country other than the approved destination.
Any diversion or reexport contrary to the export control laws and regulations of Japan and/or the country of destination is prohibited.
8. Please contact Renesas Technology Corp. for further details on these materials or the products contained therein.



RENESAS SALES OFFICES

<http://www.renesas.com>

Refer to "<http://www.renesas.com/en/network>" for the latest and detailed information.

Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A
Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited

Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology Hong Kong Ltd.

7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong
Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd.

10th Floor, No.99, Fushing North Road, Taipei, Taiwan
Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology (Shanghai) Co., Ltd.

Unit2607 Ruijing Building, No.205 Maoming Road (S), Shanghai 200020, China
Tel: <86> (21) 6472-1001, Fax: <86> (21) 6415-2952

Renesas Technology Singapore Pte. Ltd.

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632
Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd.

Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea
Tel: <82> 2-796-3115, Fax: <82> 2-796-2145

Renesas Technology Malaysia Sdn. Bhd.

Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: <603> 7955-9390, Fax: <603> 7955-9510